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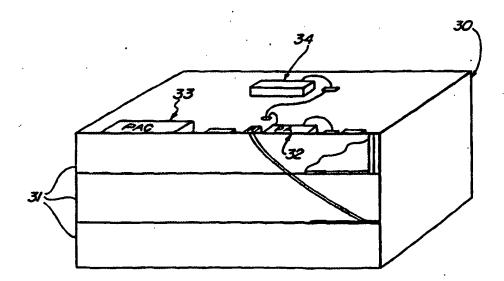
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(54) Title: MULTI-LAYER CARRIER MODULE FOR POWER AMPLIFIER



(57) Abstract

A single multi-layer carrier module (30) is disclosed which carries the power amplifier (32) components in a GSM mobile digital cellular telephone. In a first embodiment of the present invention the power amplifier (32) and the power amplifier controller (33) are placed upon a ceramic or laminate carrier module (31) along with necessary connection circuitry. The carrier module (30) is then connected to the RF board. In a second preferred embodiment of the present invention the power amplifier (32), the power amplifier controller (33) and a voltage controlled oscillator (34) are placed upon the carrier module (30).

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PCT/US98/20574 WO 99/17444

MULTI-LAYER CARRIER MODULE FOR POWER AMPLIFIER

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FIELD OF THE INVENTION

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The present invention relates generally to digital wireless communication systems, and more particularly, to a power amplifier system which incorporates multiple 9 power amplifier components upon a single carrier module 10 attached to the RF circuit board. 11

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BACKGROUND OF THE INVENTION

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> Cellular telephone systems include a central base 16 station and multiple hand held mobile cellular phones. 17 The first generation of mobile cellular phones were 18 They were bulky, large, and 19 analog based systems. heavy. Further, the analog cellular phones had limited 20 that there was one allowed in 21 channel capacity, transmission per channel, causing excessive interference 22 between users and other limitations of use. 23

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The next generation of cellular phones used digital Digital technology has allowed certain technology. digital signal processing systems and modulation or transmission techniques within the cellular environment capacity larger channel а enable which communications along with reduced interference and lower error rates within the transmissions.

speed with which the public accepts 32 The phones, cellular transition between generations of 33 including the transition from the first generation 34 analog mobile phones to the next generation digital 35 phones, is dependent upon certain factors including the 36

1 cost of the phones, the ease with which they may be
2 used, the transmission quality, and other features which
3 are desired by consumers.

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While the first generation analog mobile cellular phones were relatively the size of small books and difficult to carry, the next generation of digital cellular phones are comfortably pocket sized. Further, there is a continuing desire to reduce the size and cost of mobile cellular phone systems while still enabling more functionality and electronics systems within the hand-held cellular phone unit.

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The standards currently used for digital cellular telephony are different throughout world. The most important current digital cellular telephone standards are IS-54B which is used in the United States, Global System for Mobile Communication (GSM) in Europe, and RCR-27 in Japan. Each of these standards include digital voice and data transmission capabilities.

Various bodies worldwide are currently developing new standards for the specification of even the next generation of mobile cellular telecommunications systems along with their increased functionality. Services offered by current wireless mobile systems are simply telephony and voice services supported by narrowband digital networks. However, there will be a demand for higher bandwidth services as more comprehensive data and information transmission services are provided within the digital cellular network. Thus, today's wireless interface must carry narrowband services effectively while providing the flexibility to carry higher bandwidth services as the demand increases.

PCT/US98/20574 WO 99/17444

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Within the power amplifier control loop, an RF coupler may be used at the power amplifier output in order to couple the RF output from the power amplifier A common logarithmic detector input. directional coupler known in the art is available from Murata Manufacturing Co., Ltd., Japan as part number LDC20B200H0902.

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shown within figure 2, the input to 10 logarithmic detector upon the RF122 power amplifier 11 controller should be within the range of -40 dBm to 10 12 The coupled signal is fed to the input of the RF 13 The output from the power detector on the RF122. 14 detector is a D.C. voltage that is proportional to the 15 RF power at the RF power amplifier output. 16

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The integrating error amplifier amplifies integrates the voltage difference between the detector 19. output and the power control input. The output of the integrator is fed to the gain shaping circuit which drives the gain control input of the external RF power The integrator in the integrating error amplifier. amplifier is used to stabilize the loop. The D.C. bias 24 circuitry provides voltage bias to the RF122. 25

26

A common Voltage Controlled Oscillator may also be 27 provided on the RF board as an input drive to the power 28 The Voltage Controlled Oscillator 29 amplifier. within a phase locked loop at the power amplifier input, 30 · which translates the complex spectrum up to the desired 31 channel within the transmit band. A common Voltage 32 Controlled Oscillator used in this application 33 available from Murata Manufacturing Co., Ltd., Japan as 34 part number MQE550-902. 35

6:

1 radio major components the the in 2 Each of subsystem, the power amplifier, the power amplifier 3 controller, and the voltage controlled oscillator are separate components installed on the RF board which 5 requires space, connection circuitry and cost. 6

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OBJECTS OF THE INVENTION

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It therefore is an object of the present invention 12 to provide an improved digital cellular mobile phone 13 which is less expensive, smaller and easier to 14 manufacture.

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It is a further object of the present invention to provide an improved digital cellular mobile phone which has an RF circuit board which is more compact and easier to assemble.

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It is yet a further object of the present invention to provide an improved digital cellular mobile phone which has less separate components upon the RF circuit board.

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SUMMARY OF THE INVENTION

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These and other objects and advantages are achieved by the present invention by providing a single multilayer carrier module carrying the power amplifier and the power amplifier controller.

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In a first embodiment of the present invention the power amplifier and the power amplifier controller are placed upon a ceramic carrier module along with necessary connection circuitry. The carrier module is

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functional elements Representative which are . 1 currently anticipated to be included within the next 2 generation of wireless communication networks include 3 videotelephony, and high-speed 4 telephony, transmission. These services have varying and 5 distinguishable needs, transmission characteristics and 6 other requirements which affect the size, weight and 7 cost of cellular technology, and specifically the mobile 8 9 cellular phone unit.

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Figure 1 shows a graphical block diagram depiction 11 of the several major subsystems within a mobile digital 12 cellular telephone 10 used today. These subsystems 13 include a battery pack 11, a set of user interfaces 12 14 (including a microphone, a speaker, a keyboard and a 15 display), a set of digital control and/or analog device 16 for the user interfaces 17 13 processing and control systems 14, a radio subsystem 15 18 , and an antenna 16. As shown within figure 1, each of 19 the subsystems within the digital cellular phone 10 are 20 interrelated and provide power and control to each 21 22 other.

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The battery pack 11 initially provides power to 24 both the digital control and analog drivers 13 and the 25 digital processing and control systems 14. The analog 26 controls the 13 and control system 27 drivers 12, as well as the radio subsystem 28 interfaces including separate components such as a power amplifier, 29 a power amplifier controller and a voltage controlled 30 31 oscillator.

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The power amplifier system within the radio subsystem 15 provides output power for transmission. The radio subsystem 15 further includes a variety of passive and active RF components for transmission and

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1 reception, as well as the power amplifier for 2 transmission through the antenna 16. These radio 3 subsystem components are all provided on an RF board.

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A common power amplifier used in this environment 5 is an integrated circuit chip that is used within GSM 6 digital cellular systems. This is the RI 21005 RF power 7 amplifier available from Rockwell Semiconductor Systems, 8 The RI 21005 RF Newbury Park, California. 9 amplifier is a compact 20 pin Thin Shrink Small Outline 10 surface mount GSM power (TSSOP) 11 Package operating within the 880 - 915 MHZ cellular band with 12 The output match is pulsed output power up to 4 W. 13 realized outside of the power amplifier. 14

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amplifier controller 16 power integrated circuit chip that is used within GSM digital 17 This is the RF122 RF power amplifier cellular systems. 18 Rockwell Semiconductor from controller available 19 Systems, Newport Beach, California. The RF122 RF power 20 amplifier controller is an integrated, monolithic device 21 used to control the transmitted power of MOSFET and 22 MESFET power amplifiers. A graphical block diagram of 23 the RF122 is shown in figure 2. 24

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As shown in figure 2, the RF122 power amplifier 26 controller consist of two sections: an RF detector and a 27 gain controller. The RF122, in combination with a power 28 amplifier, forms a power amplifier control loop where 29 the power amplifier output power is controlled by a 30 single analog control voltage that is input to the 31 The RF122 consists of a logarithmic RF detector, 32 RF122. an integrating error amplifier, a gain shaper, and D.C. 33 The RF122 device is also packaged bias circuitry. 34 within a 20 pin Thin Shrink Small Outline Package 35 36 (TSSOP).

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1 then connected to the RF board.

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In the first embodiment of the present invention, 3 the power amplifier module sits upon an RF board within 4 a GSM digital cellular telephone, the module includes 5 (1) a power amplifier, which is a heterojunction bipolar 6 transistor, (2) a power amplifier controller, which 7 further includes an RF detector and a gain controller, 8 (3) an RF coupler attached to the module, the coupler 9 being electrically attached to an output of the power 10 . amplifier and feeding a signal to the input of the power 11 amplifier controller, (4) few passive components to 12 and output matching for the power 13 provide input amplifier and the necessary supporting circuitry for the 14 control loop, and 5) a module substrate. The power 15 amplifier, the power amplifier controller, 16 coupler are attached to the module substrate. 17 coupler is a directional coupler and separating a 18 forward power from a reflected power to maintain a 19 The module substrate includes constant output power. 20 multiple layers, the multiple layers allowing a lattice 21 of connection circuitry to be formed to allow the power 22 amplifier and the power amplifier controller 23 communicate with each other. 24

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In a second preferred embodiment of the present 26 invention the power amplifier, the power amplifier 27 controller and a voltage controlled oscillator are 28 placed upon a ceramic or laminate carrier module along 29 with necessary connection circuitry. The carrier module 30 The second preferred is then connected to the RF board. 31 is constructed similarly to the first 32 embodiment preferred embodiment, with the exception that 33 voltage controlled oscillator is attached to the top surface of the module substrate. The voltage controlled 35 oscillator is attached to the electrical input of the 36

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1 power amplifier to provide input drive.

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BRIEF DESCRIPTION OF THE DRAWINGS

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The features, organization, advantages and objects 5 of this invention will be fully understood from the 6 7 following detailed description and the accompanying The drawings contained herein are not 8 drawings. considered to be accurate depictions of the embodiments 9 of the invention, but are provided for illustrative 10 purposes only and are to be interpreted in conjunction 11 with the attached specification. 12

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Figure 1 shows a graphical block diagram depiction of the several major subsystems within a mobile digital cellular telephone.

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> 18 Figure 2 shows a graphical block diagram of a 19 common power amplifier controller known in the art.

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21 Figure 3 shows a graphical block diagram depiction 22 of a first preferred embodiment of the present 23 invention.

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25 Figure 4 shows a more detailed graphical block 26 diagram depiction of the first preferred embodiment of 27 the present invention shown in Figure 3.

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Figure 5 shows a graphical illustration of the carrier module of the preferred embodiment of the present invention.

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Figure 6 shows a graphical block diagram depiction of a second preferred embodiment of the present invention.

PCT/US98/20574 WO 99/17444

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DETAILED DESCRIPTION OF THE INVENTION

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The following description is provided to enable any person skilled in the art to make and use the invention, and sets forth the best modes presently contemplated by the inventor for carrying out this invention. modifications, however, will remain readily apparent to 8 skilled in these arts, since 9 principals of the present invention have been defined 10 herein.

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The first preferred embodiment of the present 13 14 invention is a multiple layer module power amplifier circuit chip made for GSM digital cellular telephones. 15 multiple layer module of the first preferred 16 embodiment contains a heterojunction bipolar transistor 17 power amplifier and a power amplifier controller which 18 19 meet the GSM specification.

20

A block diagram depiction of the first preferred 21 embodiment of the present invention is illustrated in 22 23 figure 3, and includes a power amplifier 21, a power amplifier controller 22 and a coupler 23. As shown 24 figure 3, the power amplifier receives the digital RF 25 input 24, and outputs a signal through the coupler 23. 26 The power amplifier controller 22 accepts its input 25 27 from the coupler 23 in order to create a feed back loop 28 input 26 to the power amplifier 21. 29

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detailed block diagram of the more Α preferred embodiment of the present invention is shown As shown in figure 4, the power amplifier in figure 4. controller of the preferred embodiment consists of two RF detector and a gain controller 35 sections: an The power amplifier controller and the 36 (integrator).

power amplifier form a power amplifier control loop where the power amplifier output power is controlled by a single analog control voltage.

In the event of a poor voltage standing wave ratio, the preferred embodiment to the present invention includes a built-in directional coupler which separates the forward power from the reflected power in order to maintain a constant output power. In the preferred embodiment of the present invention the power amplifier is designed with a bipolar gallium arsenide process that allows single supply operation while maintaining high efficiency and excellent dynamic range.

A graphical illustration of the carrier module of the preferred embodiment of the present invention is depicted in figure 5. As the shown in figure 5, the carrier module 30, has multiple layers 31, which allows circuitry to be inlaid to enable the various power amplifier components to electrically communicate and interact with one another.

As shown in figure 5, in the preferred embodiments of the present invention, the power amplifier 32, the power amplifier controller 33 and a voltage control oscillator 34 all sit upon the top layer of the multiple layer carrier module 30. A coupler is inlaid below the surface of the carrier module on other lower layers 31. Other connection circuitry is also embedded within the multiple layers of the carrier module 30. Common insulation or packaging is provided in order to protect the power amplifier components attached to the top surface of the carrier module substrate.

The carrier module of the preferred embodiment of the present invention is ceramic or laminate. In the

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1 preferred embodiment of "the present invention the 2 substrate is a B.T. laminate available from Details, 3 Inc., Anaheim, California.

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second preferred embodiment of the present 5 · A invention is depicted in the block diagram illustration 6 shown in figure 6. As shown in figure 6, the carrier module 40 includes the same components as the carrier module depicted in figure 3 along with a voltage controlled oscillator 41. The second preferred 10 embodiment illustrated in figure 6 operates in the same 11 manner as the power amplifier system illustrated in -12 figure 3 with the addition that the voltage controlled 13 oscillator 41 is integrated on the carrier module to 14 drive the power amplifier. 15

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Those skilled in the art will appreciate that 17 various adaptations and modifications of the just 18 embodiment can be used and 19 described preferred configured without departing from the scope and spirit 20 Therefore, it is to be understood 21 of the invention. that, within the scope of the appended claims, the 22 invention may be practiced other than as specifically 23 described herein. 24

ì	. 12 " CLAIMS
2	•
3	What is Claimed Is:
4.	
1	A power amplifier module upon an RF board
2	within a digital cellular telephone, the module
3	comprising:
4	
5	a power amplifier;
6	
7	a power amplifier controller; and
8	
9	a module substrate, the power amplifier and
10	the power amplifier controller attached
11	to the module substrate, the substrate
12	heing attachable to the RF hoard

- 1 2. The module of Claim 1 wherein the power
- 2 amplifier is a heterojunction bipolar transistor.
- 3. The module of Claim 1 wherein the module.
- 2 meets a GSM specification.
- 1 4. The module of Claim 1, further comprising
- 2 an RF coupler attached to the module, the coupler being
- 3 electrically attached to an output of the power
- 4 amplifier.
- 1 5. The module of Claim 4, wherein the coupler
- 2 feeds a signal to the input of the power amplifier
- 3 controller.
- 1 6. The module of Claim 5, wherein the coupler
- 2 is a directional coupler which separates a forward power
- 3 from a reflected power to maintain a constant output
- 4 power.
- 7. The module of claim 1, wherein the power
- 2 amplifier controller further includes an RF detector and
- 3 a gain controller.
- 1 8. The module of Claim 1, wherein the power
- 2 amplifier receives a single analog control voltage

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3 signal and the power amplifier and the power amplifier.

- 4 controller form a power amplifier control loop.
- 9. The module of Claim 1, wherein the power
- 2 amplifier is designed with a bipolar gallium arsenide
- 3 process.
- 1 10. The module of Claim 1, wherein the module
- 2 substrate further comprises multiple layers, the
- 3 multiple layers providing a lattice of connection
- 4 circuitry to allow the power amplifier an the power
- 5 amplifier controller to communicate with each other.
- 1 11. The module of Claim 10, wherein the power
- 2 amplifier, the power amplifier controller and a voltage
- 3 controlled oscillator sit upon a top surface of the
- 4 multiple layer module substrate.

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1	12. The module of Claim 10, wherein a coupler
2	is inlaid upon the multiple layer module substrate, the
3	coupler being inlaid upon layers of the substrate below
4	a top layer.
1	13. The module of Claim 10, wherein the
2	substrate is BT laminate.
1	14. The module of Claim 1, further comprising
1	14. The module of Claim 1, further comprising
2	a voltage controlled oscillator attached to the module
3.	substrate, the voltage controlled oscillator being
4	connected at an input to the power amplifier.
1	15. A power amplifier module upon an RF board
2	within a digital cellular telephone, the module
3	comprising:
4.	
5	a power amplifier, the power amplifier being a
6	heterojunction bipolar transistor;
7	
8	a power amplifier controller, the power
9	amplifier controller further including an
10	RF detector and a gain controller;
11	
12	an RF coupler attached to the module, the
13	coupler being electrically attached to an
14	output of the power amplifier, the
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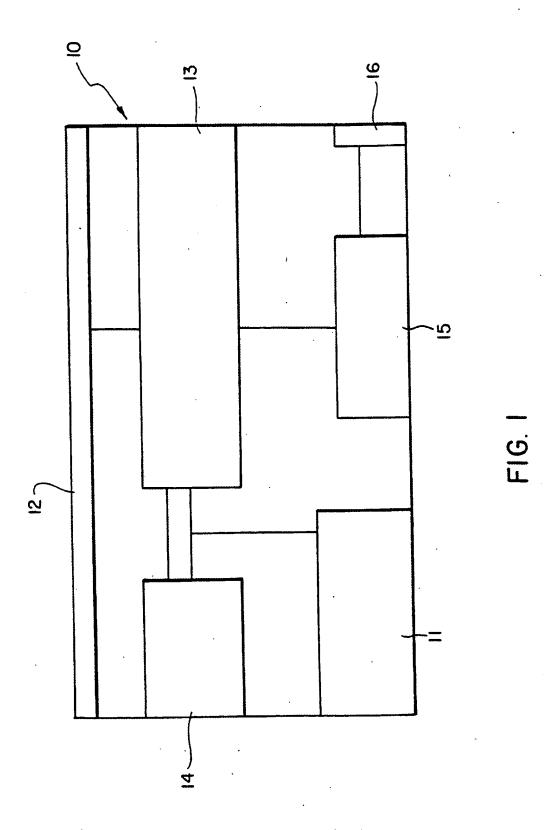
	16
15	coupler feeding a signal to the input of
16	the power amplifier controller, the
17	coupler being a directional coupler and
18	separating a forward power from a
19	reflected power to maintain a constant
20	output power;
21	
22	a module substrate, the power amplifier, the
23	power amplifier controller, and the
24	coupler attached to the module substrate,
25	the module substrate further comprises
26	multiple layers, the multiple layers
27	providing a lattice of connection
28	circuitry to allow the power amplifier
29	and the power amplifier controller to
30	communicate with each other, the module
31	substrate being attachable to the RF
32	board.
1	16. The module of Claim 15, wherein the

- module meets a GSM specification.
- 17. The module of Claim 15, wherein the power 1
- amplifier receives a single analog control voltage
- signal and the power amplifier and the power amplifier
- controller form a power amplifier control loop.
- 18. The module of Claim 15, wherein the power 1

17

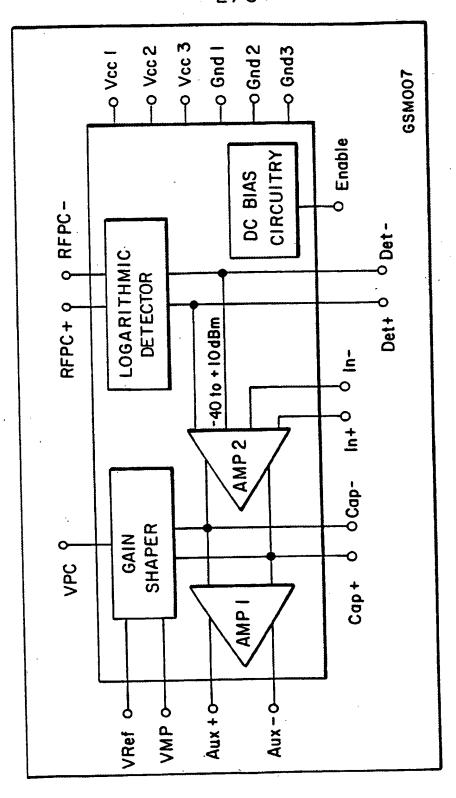
- 2 amplifier, the power amplifier controller and a voltage
- 3 controlled oscillator sit upon a top surface of the
- 4 multiple layer module substrate.
- 1 19. The module of Claim 15, wherein the
- 2 coupler is inlaid upon the multiple layer module
- 3 substrate, the coupler being inlaid upon layers of the
- 4 substrate below a top layer.
- 1 20. The module of Claim 15, further
- 2 comprising a voltage controlled oscillator, the voltage
- 3 controlled oscillator being electrically connected at an
- 4 input to the power amplifier, the voltage controlled
- 5 oscillator being attached to the top surface of the
- 6 module substrate.

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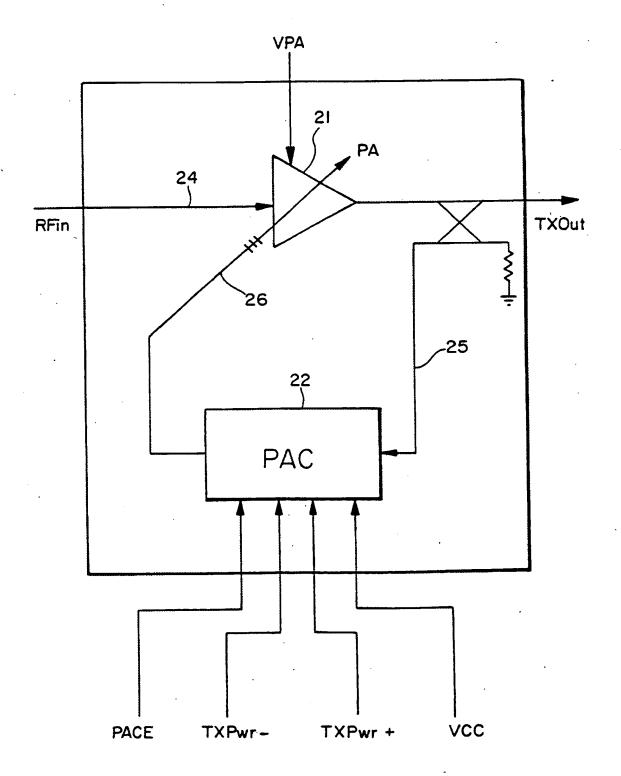
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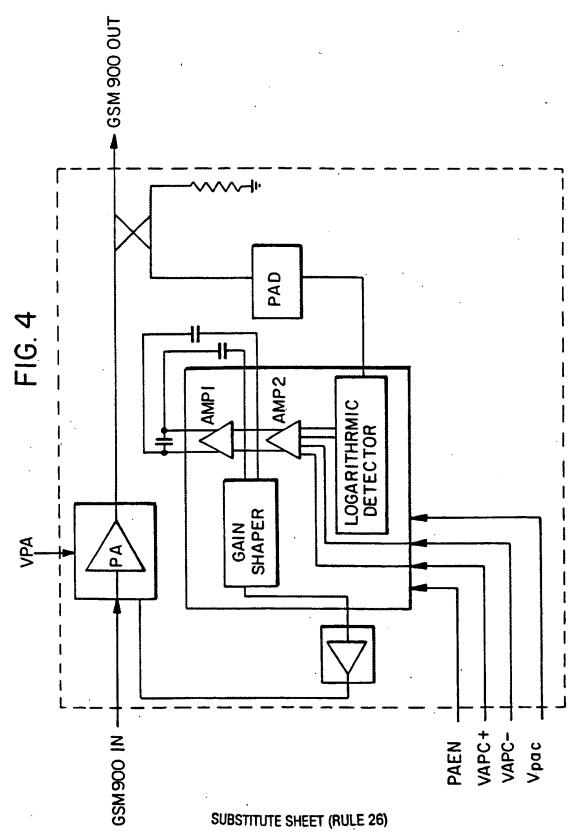


F16. 2

3/6 FIG. 3



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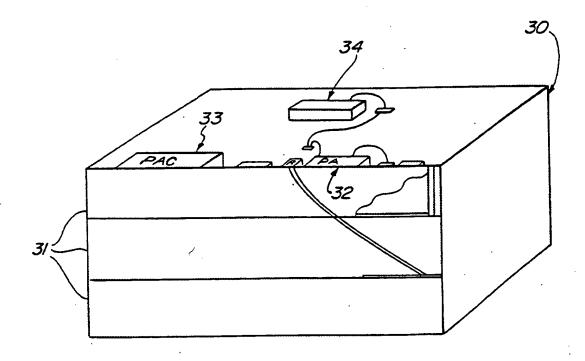
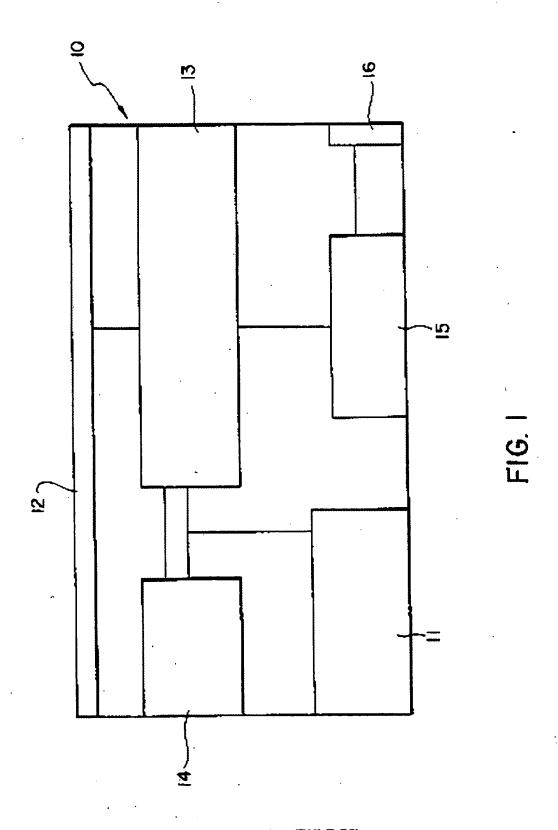
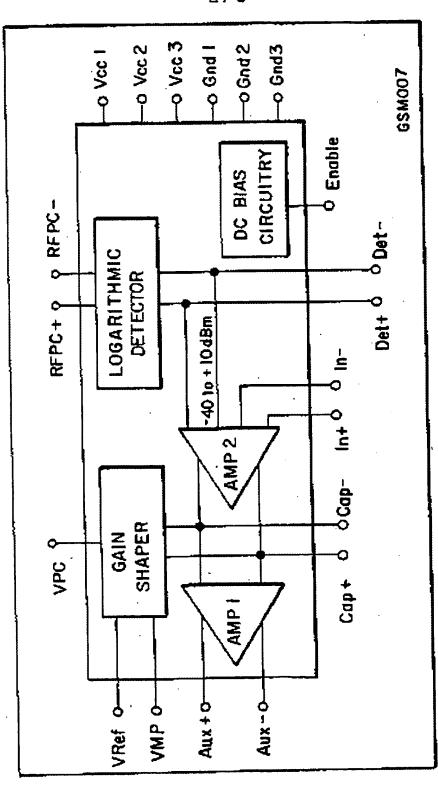


FIG. 5

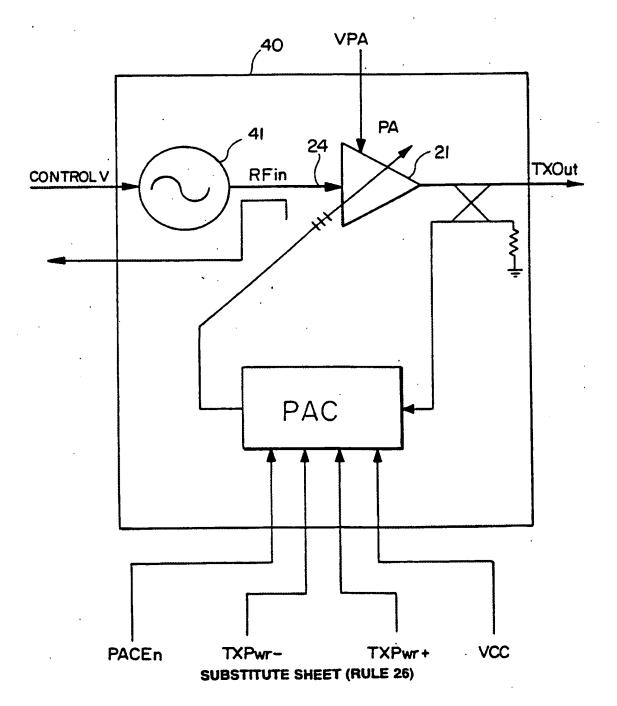


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FIG. 6

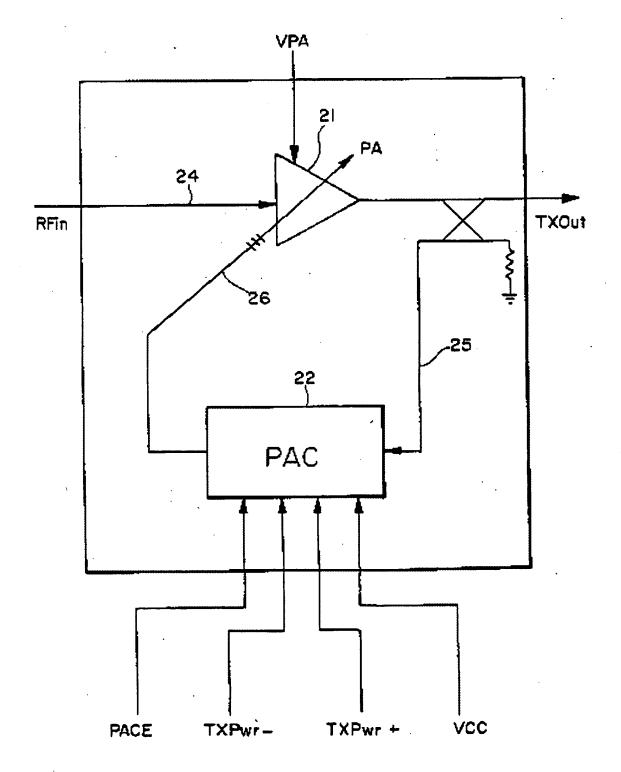


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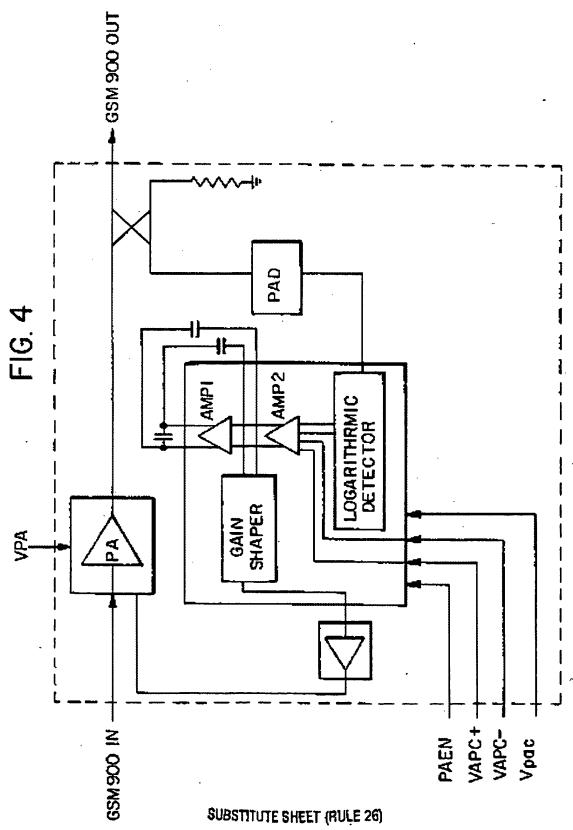
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C. DOC	CUMENTS CONSIDERED TO BE RELEVANT				
Category®	Citation of document, with indication, where appr	ropriate, of the relevant passages Rel	evant to claim No.		
х	US 5,142,239 A (BRAYTON ET AL.) see Fig. 2 and col. 4, lines 64-66.	25 August 1992 (25/08/92), 1-20			
X	US 5,450,046 A (KOSUGI ET AL.) 12 see Fig. 6 and col. 6, lines 50-62.	September 1995 (12/09/95), 1-20	0		
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3/6 *FIG. 3*



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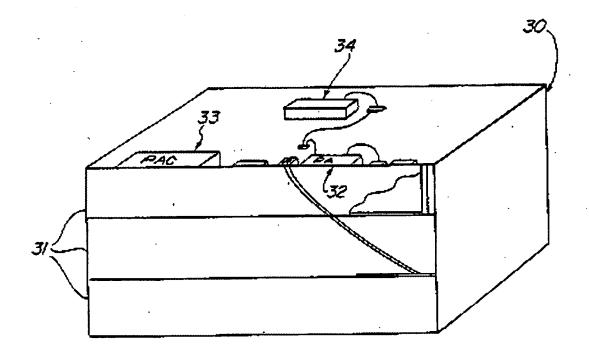


FIG. 5

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FIG. 6

MCM PA / PAC / VCO

